

HAT2174H

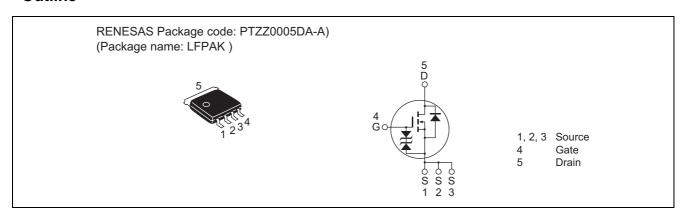
Silicon N Channel Power MOS FET Power Switching

REJ03G0041-0400 Rev.4.00 Dec 11, 2006

Features

- Capable of 8 V gate drive
- Low drive current
- High density mounting
- Low on-resistance $R_{DS(on)} = 21 \text{ m}\Omega \text{ typ. (at } V_{GS} = 10 \text{ V})$

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	100	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	20	Α
Drain peak current	I _{D(pulse)} Note1	80	A
Body-drain diode reverse drain current	I _{DR}	20	A
Avalanche current	I _{AP} Note 2	20	A
Avalanche energy	E _{AR} Note 2	40	mJ
Channel dissipation	Pch Note3	20	W
Channel to Case Thermal Resistance	θch-C	6.25	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tch = 25°C, Rg \geq 50 Ω

3. $Tc = 25^{\circ}C$

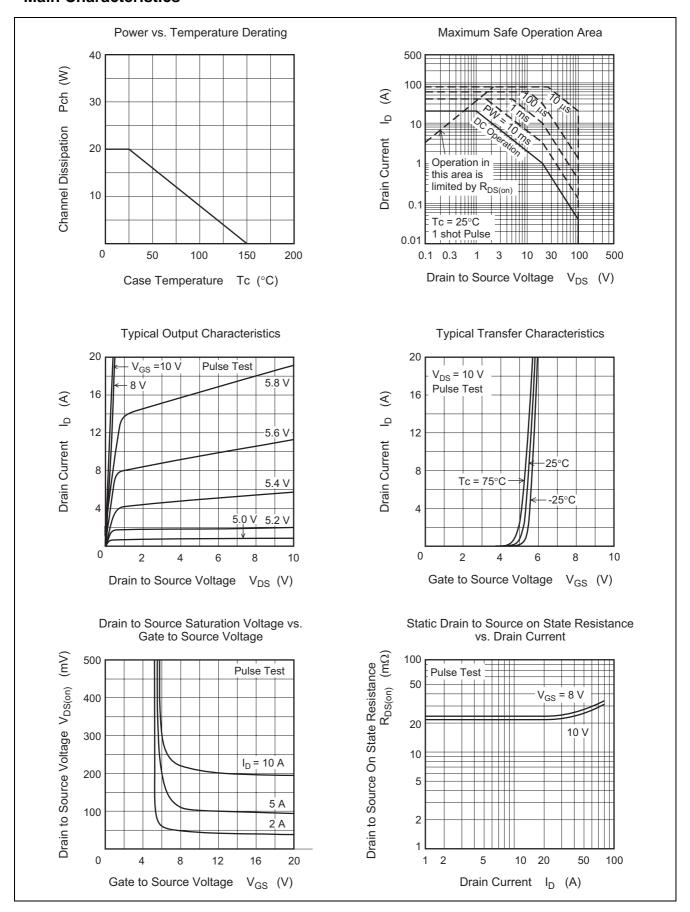
Electrical Characteristics

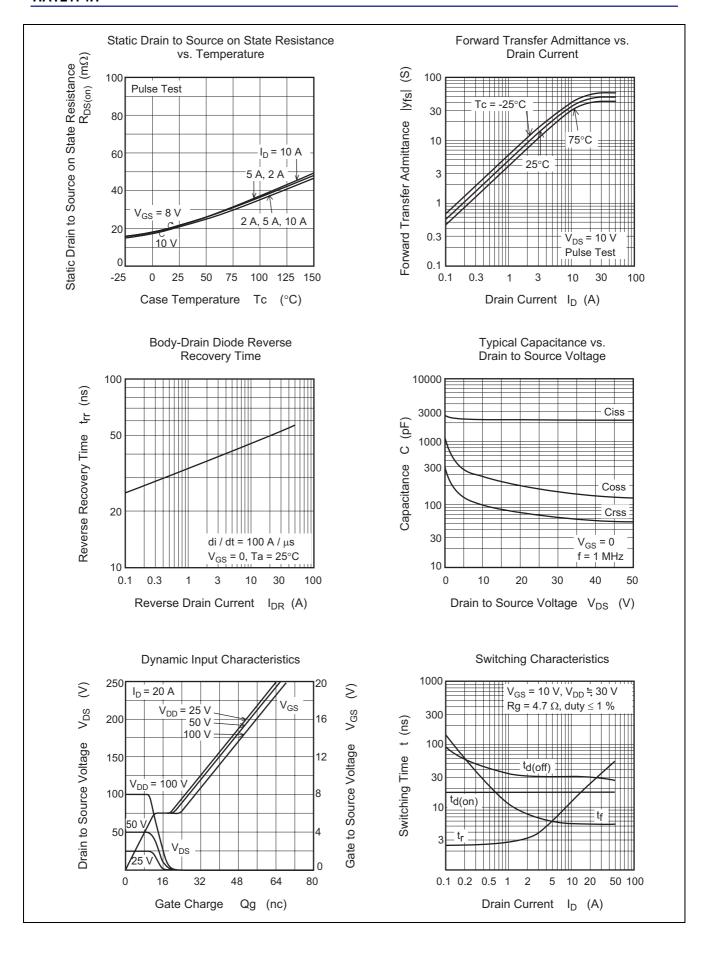
 $(Ta = 25^{\circ}C)$

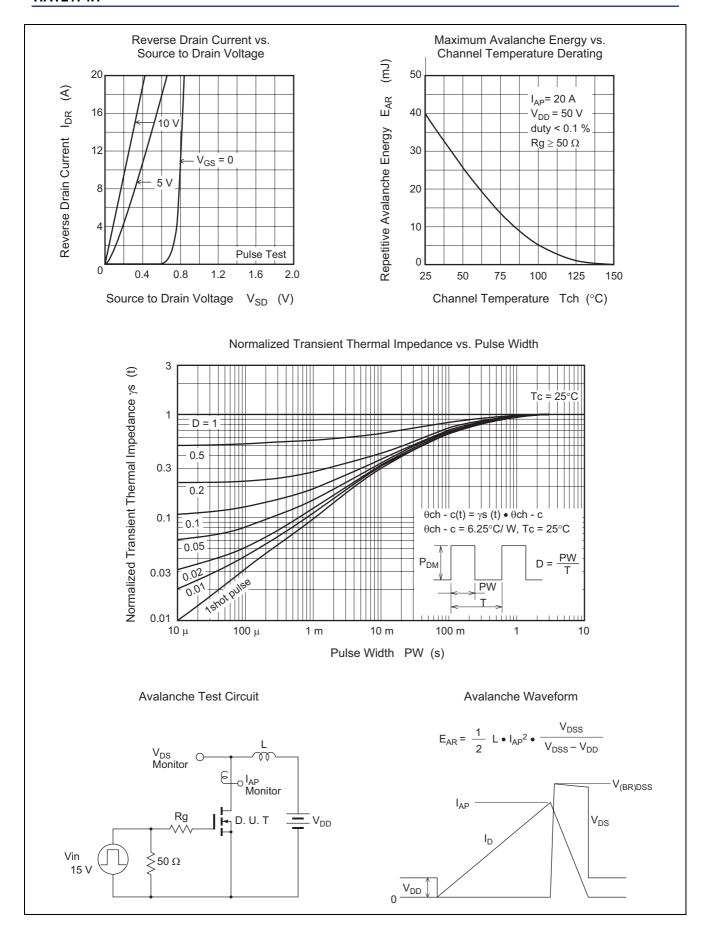
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_		1	μΑ	V _{DS} = 100 V, V _{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	4.0		6.0	V	$V_{DS} = 10 \text{ V}, I_D = 20\text{mA}$
Static drain to source on state	R _{DS(on)}	_	21	27	mΩ	$I_D = 10 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
resistance	R _{DS(on)}	_	22	30	mΩ	$I_D = 10 \text{ A}, V_{GS} = 8 \text{ V}^{\text{Note4}}$
Forward transfer admittance	y _{fs}	21	35		S	$I_D = 10 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	2280	1	pF	$V_{DS} = 10 \ V, V_{GS} = 0,$
Output capacitance	Coss	_	285		pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	100	_	pF	
Gate Resistance	Rg	_	0.5	_	Ω	
Total gate charge	Qg	_	33.5	_	nC	$V_{DD} = 50 \text{ V}, V_{GS} = 10 \text{ V},$
Gate to source charge	Qgs	_	12.4	_	nC	I _D = 20 A
Gate to drain charge	Qgd	_	8.4	_	nC	
Turn-on delay time	t _{d(on)}	_	18	_	ns	$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A},$
Rise time	t _r	_	13	_	ns	$V_{DD} \cong 30 \text{ V}, \text{ R}_{L} = 3 \Omega,$
Turn-off delay time	t _{d(off)}	_	31	_	ns	$Rg = 4.7 \Omega$
Fall time	t _f	_	5.5	_	ns	
Body-drain diode forward voltage	V_{DF}	_	0.84	1.10	V	$IF = 20 A$, $V_{GS} = 0$ Note4
Body-drain diode reverse recovery	t _{rr}	_	50	_	ns	IF = 20 A, V _{GS} = 0
time						di _F / dt = 100 A/ μs

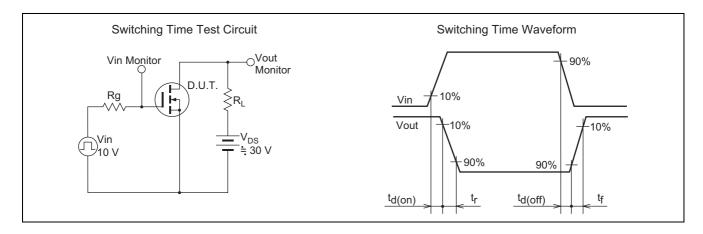
Notes: 4. Pulse test

Main Characteristics

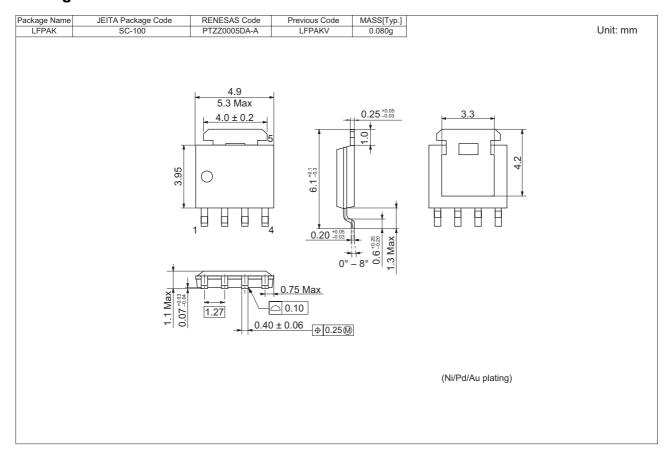








Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
HAT2174H-EL-E	2500 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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